# COMPACT AND HIGH SENSITIVE SLOTTED BRAGG GRATING ON SOI PLATFORM FOR REFRACTIVE INDEX SENSOR

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## Introduction

Essentials for silicon photonics are lowering size and cost without affecting effectiveness for various performances. One of the effective sensing elements with smaller footprints and few step fabrication is a micro ring resonators (MRR). Using slotted waveguides and sub-wavelength gratings (SWG) in MRRs have shown higher sensitivity [1-2]. Recently combination of the SWG and slotted waveguides exhibited even higher performances [3]. In the study, we propose a sensor with slotted SWGs on straight waveguide where Bragg grating (BG) reflection condition is fulfilled.

#### Structures and operation principle

In order to lower losses two different gratings in one period are also investigated, as shown in Fig. 1. For single etch-step process we adopted a high mesa waveguide of 340nm height with slots of no smaller than 30nm wide due to fabrication limit. We select waveguide parameters to obtain Bragg reflection condition:

#### $2\Lambda n_{eff} = m\lambda_B$ ,

where  $\Lambda$  is a period, m an order of Bragg diffraction, n<sub>eff</sub> a waveguide effective index and  $\lambda_B$  a centre wavelength of the Bragg stop-band. For the lowest losses m should be one. An operation wavelength is near 1.55 µm. Refractive indices of a surrounding medium is 1.333 for water and 1.343 with alcohol.

#### Simulated results

With single grating type in one period we found that 3 slot case where the outer slot widths have half of middle width are best having a high sensitivity S = 605 nm/RIU, an extinction ratio ER =26 dB, a loss -5.3 dB and a sensor length as small as 6.5  $\mu$ m. For two types of gratings in one period 3 to 4 slot case were the best with S = 636 nm/RIU, ER =33.3 dB, as shown in Fig. 2, and a loss -4.6 dB for a sensor length 17.6  $\mu$ m.

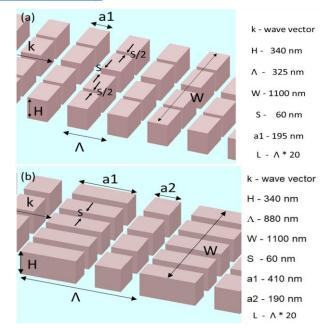
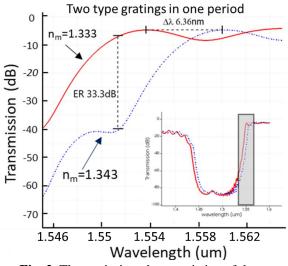


Fig. 1. (a) Single and (b) double BG structures.



**Fig. 2.** Thansmission characteristics of the proposed device under the refractive index change. Inlet shows the whole stop-band.

#### References

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